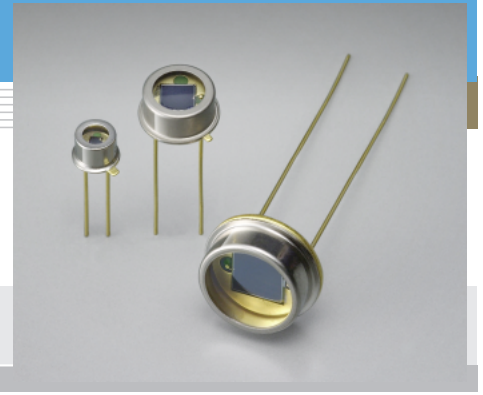


Si photodiode S1336 series

UV to near IR for precision photometry



Features

- High sensitivity
- Low capacitance
- High reliability

Applications

- Analytical instruments
- Optical measurement equipment

■ General ratings / Absolute maximum ratings

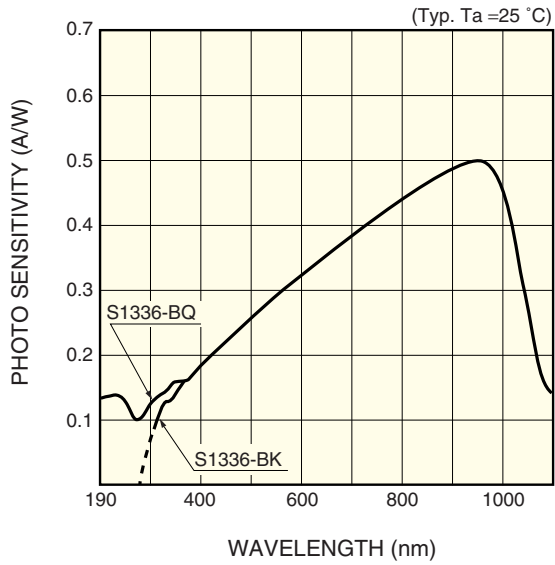
Type No.	Dimensional outline/ Window material *	Package (mm)	Active area size (mm)	Effective active area (mm ²)	Absolute maximum rating		
					Reverse voltage V _R Max. (V)	Operating temperature T _{opr} (°C)	Storage temperature T _{stg} (°C)
S1336-18BQ	①/Q	TO-18	1.1 × 1.1	1.2	5	-20 to +60	-55 to +80
S1336-18BK	①/K					-40 to +100	-55 to +125
S1336-5BQ	②/Q	TO-5	2.4 × 2.4	5.7		-20 to +60	-55 to +80
S1336-5BK	②/K					-40 to +100	-55 to +125
S1336-44BQ	②/Q					-20 to +60	-55 to +80
S1336-44BK	②/K					-40 to +100	-55 to +125
S1336-8BQ	③/Q	TO-8	5.8 × 5.8	33		-20 to +60	-55 to +80
S1336-8BK	③/K					-40 to +100	-55 to +125

■ Electrical and optical characteristics (Typ. T_a=25 °C, unless otherwise noted)

Type No.	Spectral response range λ (nm)	Peak sensitivity wavelength λ_p (nm)	Photo sensitivity S (A/W)			Short circuit current I _{sc} 100 lx		Dark current I _D V _R =10 mV Max. (pA)	Temp. coefficient of I _D T _{CID} (times/°C)	Rise time t _r V _R =0 V R _L =1 kΩ (μs)	Terminal capacitance C _t V _R =0 V f=10 kHz (pF)	Shunt resistance R _{sh} V _R =10 mV		NEP (W/Hz ^{1/2})					
			λ_p	200 nm		Min.	Typ.					Min.	Typ.						
				Min.	Typ.										(GΩ)	(GΩ)			
S1336-18BQ	190 to 1100	960	0.5	0.10	0.12	0.33	1	1.2	20	1.15	20	0.5	2	5.7 × 10 ⁻¹⁵					
S1336-18BK	320 to 1100														-	-			
S1336-5BQ	190 to 1100														0.10	0.12	4	5	30
S1336-5BK	320 to 1100														-	-	8	10	50
S1336-44BQ	190 to 1100														0.10	0.12	22	28	100
S1336-44BK	320 to 1100														-	-			
S1336-8BQ	190 to 1100														0.10	0.12			
S1336-8BK	320 to 1100														-	-			

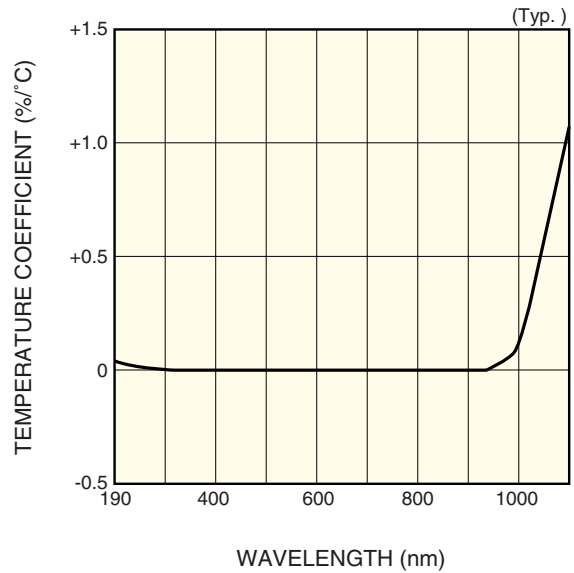
* Window material, K: borosilicate glass, Q: quartz glass

■ Spectral response



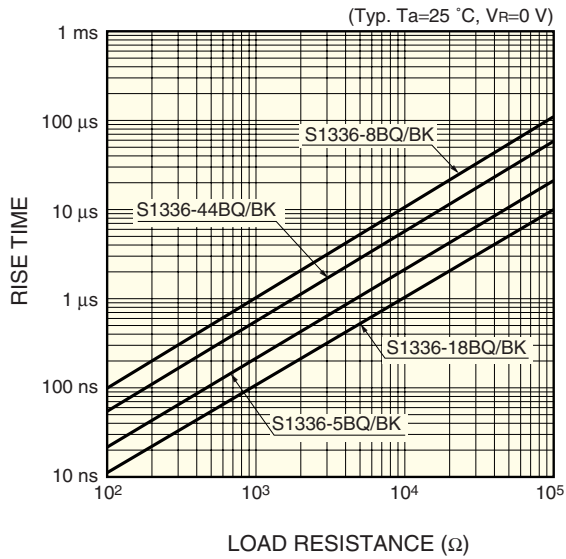
KSPDB0098EA

■ Photo sensitivity temperature characteristic



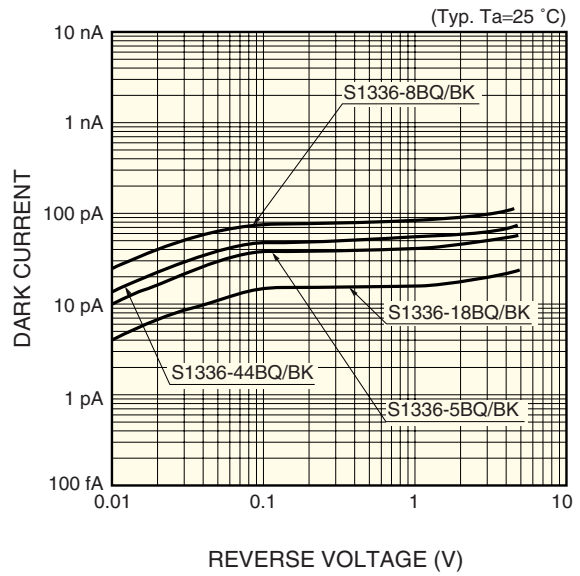
KSPDB0053EB

■ Rise time vs. load resistance



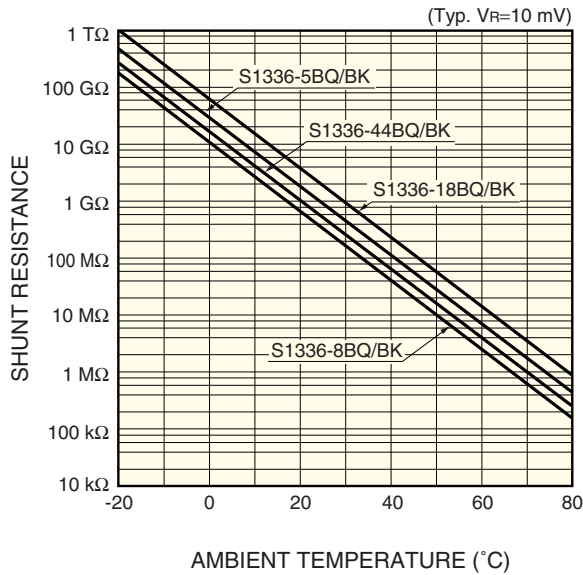
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■ Dark current vs. reverse voltage



KSPDB0100EA

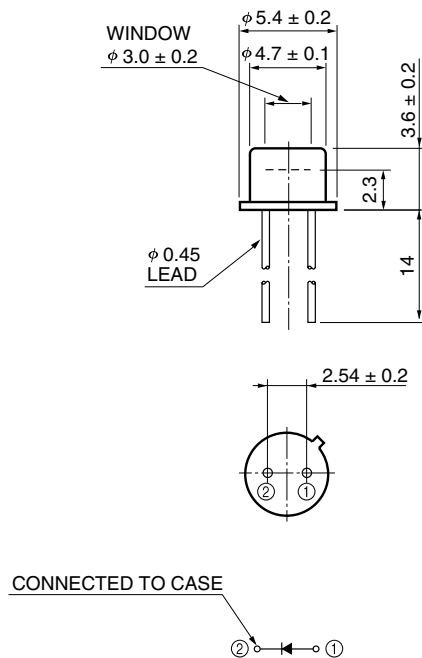
■ Shunt resistance vs. ambient temperature



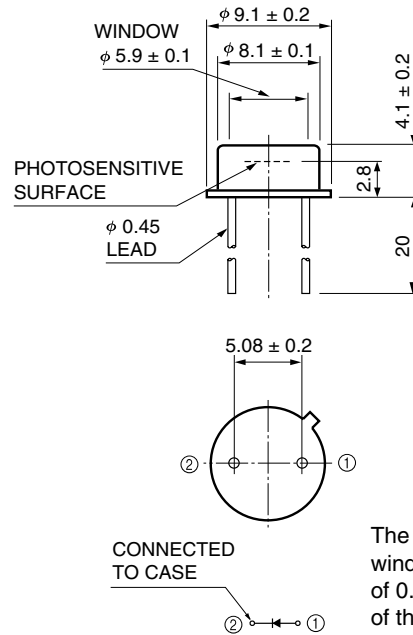
KSPDB0101EA

■ Dimensional outlines (unit: mm)

① S1336-18BQ/-18BK



② S1336-5BQ/K, S1336-44BQ/K

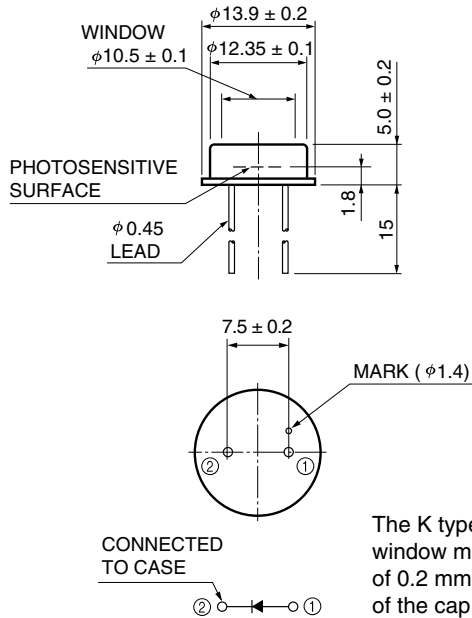


The K type borosilicate glass window may extend a maximum of 0.2 mm above the upper surface of the cap.

KSPDA0102EB

KSPDA0103EA

③ S1336-8BQ/-8BK



KSPDA0104EA

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HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Higashi-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81) 53-434-3311, Fax: (81) 53-434-5184, <http://www.hamamatsu.com>

U.S.A.: Hamamatsu Corporation: 360 Foothill Road, P.O.Box 6910, Bridgewater, N.J. 08807-0910, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 08152-3750, Fax: (49) 08152-2658

France: Hamamatsu Photonics France S.A.R.L.: 19, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Smidesvägen 12, SE-171 41 Solna, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.R.L.: Strada della Moia, 1/E, 20020 Arese, (Milano), Italy, Telephone: (39) 02-935-81-733, Fax: (39) 02-935-81-741

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